Features

- High Dynamic Range for AM and FM
- Integrated AGC for FM
- High Intercept Point 3rd-order for FM
- FM Amplifier Adjustable to Various Cable Impedances
- High Intercept Point 2nd-order for AM
- Low-noise Output Voltage
- Low Power Consumption



Electrostatic sensitive device.

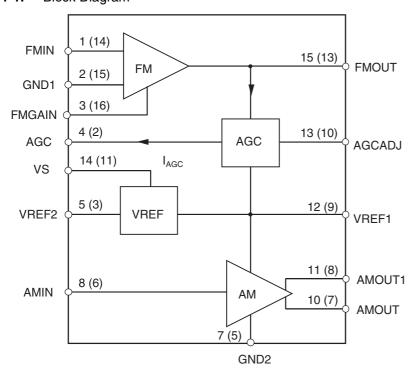
Observe precautions for handling.



1. Description

The ATR4254 is an integrated low-noise AM/FM antenna impedance matching circuit in BiCMOS technology. The device is designed specifically for car applications and is suitable for windshield and roof antennas.

Figure 1-1. Block Diagram



() Pin numbers in brackets = QFN16 4 × 4 package



Low-noise AM/FM Antenna Impedance Matching IC

ATR4254

Rev. 4879A-AUDR-09/05





2. Pin Configuration

Figure 2-1. Pinning SO16

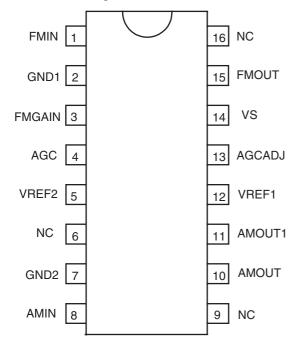


Figure 2-2. Pinning QFN16 4×4

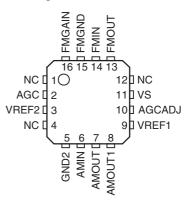


Table 2-1. Pin Description

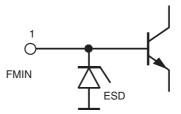
Pin SSO16	Pin QFN16	Symbol	Function	
1	14	FMIN	FM input	
2	15	GND1	Ground for FM part	
3	16	FMGAIN	FM gain adjustment	
4	2	AGC	AGC output	
5	3	VREF2	Reference voltage 2 output	
6	1	NC	Not connected	
7	5	GND2	Ground for AM part	
8	6	AMIN	AM input	
9	4	NC	Not connected	
10	7	AMOUT	AM output	
11	8	AMOUT1	AM output	
12	9	VREF1	Reference voltage 1 output	
13	10	AGCADJ	Adjustment FM wide-band AGC threshold	
14	11	VS	Supply voltage	
15	13	FMOUT	FM output	
16	12	NC	Not connected	

3. Pin Description

3.1 **FMIN**

The input of the FM amplifier, FMIN, is a bipolar transitor's base. A resistor or a coil is connected between FMIN and VREF2. If a coil is used, the noise performance is excellent.

Figure 3-1. Internal Circuit at Pin FMIN



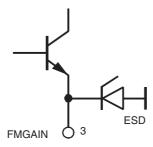
3.2 GND1

To avoid cross-talk between AM and FM signals, the circuit has two separate ground pins. GND1 is the ground for the FM part.

3.3 FMGAIN

The DC current of the FM amplifier transistor is adjusted by an external resistor which is connected between FMGAIN and GND1. To influence the AC gain of the amplifier, a resistor is connected in series to a capacitor between FMGAIN and GND1. The capacitor has to shorten frequencies of 100 MHz.

Figure 3-2. Internal Circuit at Pin FMGAIN



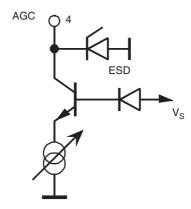
3.4 AGC

DC current flows into the AGC pin at high FM antenna input signals. This current has to be amplified via the current gain of an external PNP transistor that feeds a PIN diode. This diode dampens the antenna's input signal and protects the amplifier input against overload. The maximum current which flows into the AGC pin is approximately 1 mA. In low-end applications, the AGC function is not necessary and the external components can therefore be omitted.





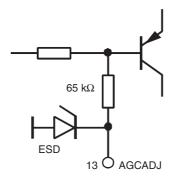
Figure 3-3. Internal Circuit at Pin AGC



3.5 AGCADJ

The threshold of the AGC can be adjusted by varying the DC current at pin AGCADJ. If pin AGCADJ is connected directly to GND1, the threshold is set to 96 dB μ V at the FM amplifier output. If a resistor is connected between AGCADJ and GND1, the threshold is shifted to higher values with increasing resistances. If AGCADJ is open, the threshold is set to 106 dB μ V.

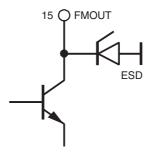
Figure 3-4. Internal Circuit at Pin AGCADJ



3.6 FMOUT

The FM amplifier output is an open collector of a bipolar RF transistor. It should be connected to V_S via a coil.

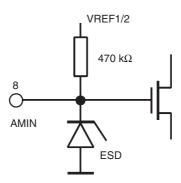
Figure 3-5. Internal Circuit at Pin FMOUT



3.7 AMIN

The AM input has an internal bias voltage. The DC voltage at this pin is $V_{Ref1/2}$. The input resistance is about 470 k Ω The input capacitance is less than 10 pF.

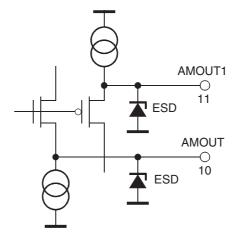
Figure 3-6. Internal Circuit at Pin AMIN



3.8 AMOUT, AMOUT1

The buffered AM amplifier consists of a complementary pair of CMOS source followers. The transistor gates are connected to AMIN. The pin AMOUT is the NMOS transistor's source, pin AMOUT1 is the PMOS transistor's source. Due to the two different DC levels of these pins, they have to be connected together via an external capacitor of about 100 nF. This technique can achieve an excellent dynamic range.

Figure 3-7. Internal Circuit at Pins AMOUT1 and AMOUT



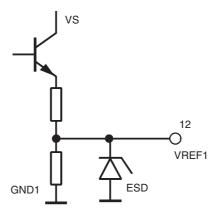
3.9 VREF1

VREF1 is the stabilized voltage for the AM amplifier and the AGC block. To achieve excellent noise performance at LW frequencies, it is recommended that this pin be connected to ground via an external capacitor of about 1 μ F.





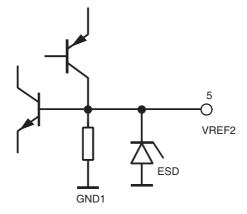
Figure 3-8. Internal Circuit at Pin VREF1



3.10 VREF2

For the DC biasing of the FM amplifier, a second voltage reference circuit is integrated. Since the collector current is temperature independent, the output voltage has a negative temperature coefficient of about –1 mV/K. To stabilize this voltage, an external capacitor to ground of a few nF is recommended.

Figure 3-9. Internal Circuit at Pin VREF2



3.11 GND2

GND2 is the ground for the AM amplifier.

4. Functional Description

The ATR4254 is an integrated AM/FM antenna impedance matching circuit. It compensates cable losses between the antenna (for example, windshield, roof or bumper antennas) and the car radio, which is usually placed far away from the antenna.

The FM amplifier provides excellent noise performance. External components are used to adjust the gain and the input-output matching impedance. Therefore, it is possible to adjust the amplifier to various cable impedances (usually 50Ω , 75Ω or 150Ω). To protect the amplifier against input overload, an Automatic Gain Control (AGC) is included on the chip. The AGC observes the AC voltage at the FM amplifier output, rectifies this signal, and delivers DC current to dampen the input antenna signal via an external PIN diode. The threshold for the AGC is adjustable. Simple and temperature-compensated biasing is possible due to the integrated voltage reference $V_{\rm Ref2}.$

The AM part consists of a buffer amplifier. The voltage gain of this stage is approximately one. The input resistance is 470 k Ω , the input capacitance less than 10 pF. The output resistance is 125 Ω An excellent dynamic range is achieved due to the complementary CMOS source follower stage.

5. Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Reference point is ground (pins 2 and 7)

Parameters	Symbol	Value	Unit	
Supply voltage	V _S	8.8	V	
Power dissipation, P _{tot} at T _{amb} = 85°C	P _{tot}	460	mW	
Junction temperature	T _j	150	°C	
Ambient temperature	T _{amb}	-40 to +85	°C	
Storage temperature	T _{stg}	-50 to +150	°C	
Electrostatic handling (HBM at ESD S.5.1)	±V _{ESD}	±1000	V	

6. Thermal Resistance

Parameters	Symbol	Value	Unit	
Junction ambient	R _{thJA}	140	K/W	





7. Electrical Characteristics

 V_S = 8V, T_{amb} = 25° C, unless otherwise specified (see Figure 7-1 on page 9).

Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit
Supply voltage		14	Vs	7.2	8	8.8	V
Supply currents		14	I _S	3.5	4.8	5.6	mA
Reference voltage 1 output (I ₁₂ = 0)		12	V _{Ref1}	5.1	5.4	5.7	V
Reference voltage 2 output (I ₅ = 0)		5	V _{Ref2}	2.3	2.6	2.8	V
Temperature dependence of VREF2		5	V _{Ref2} /∆T		-1		mV/K
AM Amplifier							
Input resistance		8	R _{AMIN}		470		kΩ
Input capacitance		8	C _{AMIN}			10	pF
Output resistance		10	R _{OUT}		125		Ω
Voltage gain		8, 10	а		0.85		
Output noise voltage (rms value)	S1 switched to 2 B = 6 kHz 150 kHz to 300 kHz 500 kHz to 6.5 kHz	10	V _{N1} V _{N2}		-2 -6		dΒμV dΒμV
2nd harmonic	S2 switched to 1 f _{AMIN} = 500 kHz Output voltage = 110 dBµV	10			-65		dBc
FM Amplifier	1		.		•		
Supply current limit	I_{AGC} , $I_{AGCADJ} = 0A$	15	I ₁₅		33	35	mA
Input resistance	f = 100 MHz	1	R _{FMIN}		50		Ω
Output resistance	f = 100 MHz	15	R _{FMOUT}		50		Ω
Power gain	f = 100 MHz	1, 15	G		5		dB
Output noise voltage	f = 100 MHz B = 120 kHz	15	V _N		0		dΒμV
3rd-order output intercept	f = 100 MHz	15			132		dΒμV
AGC	1		•	•		•	
AGC input voltage threshold	f = 100 MHz S2 switched to 1; AGC threshold DC current is 10 μA at pin 4	15	V _{th1}		96		dΒμV
AGC input voltage threshold	f = 100 MHz, S2 switched to 2; AGC threshold DC current is 10 μA at pin 4	15	V _{th2}		106		dΒμV
AGC output current	AGC active		I _{AGC}			1.2	mA

Figure 7-1. Test Circuit

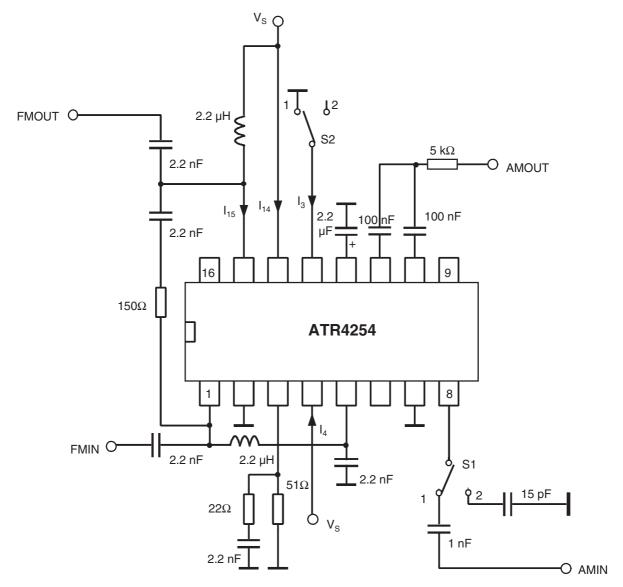
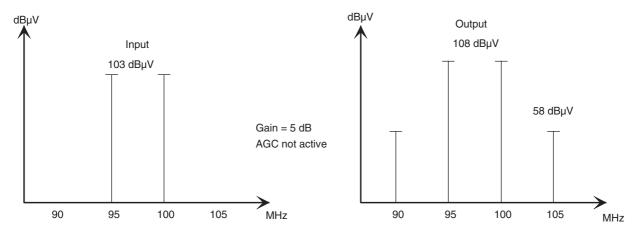
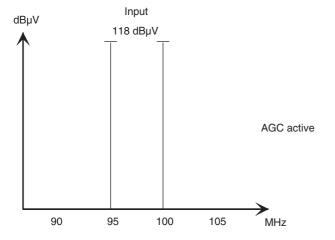
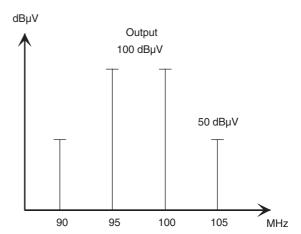




Figure 7-2. FM Intermodulation Distortion







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Figure 7-3. Test Circuit for AM Large Signal Behavior

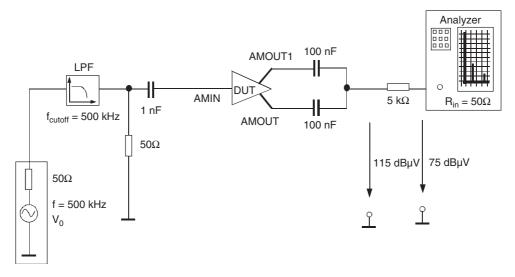


Figure 7-4. AM Harmonic Distortion

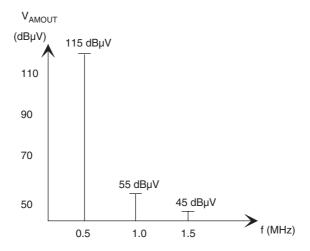
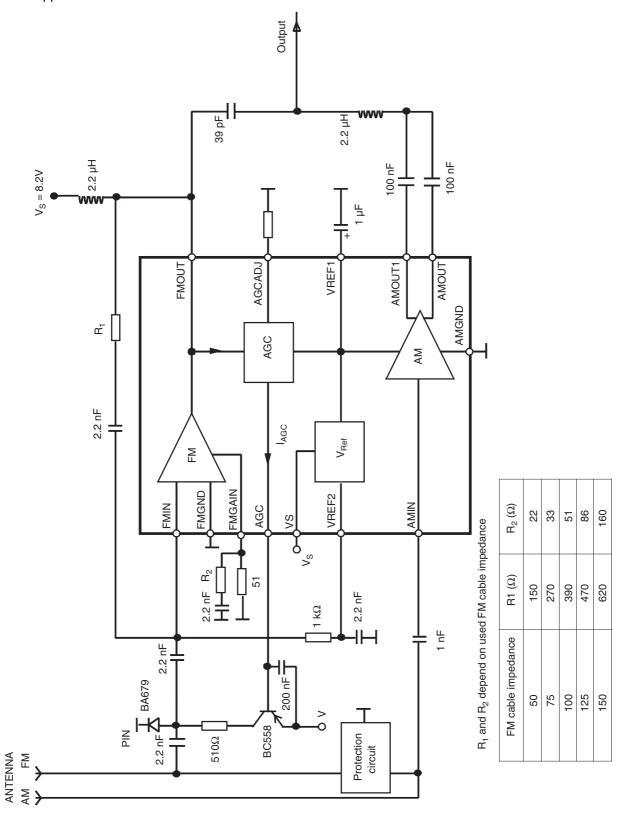




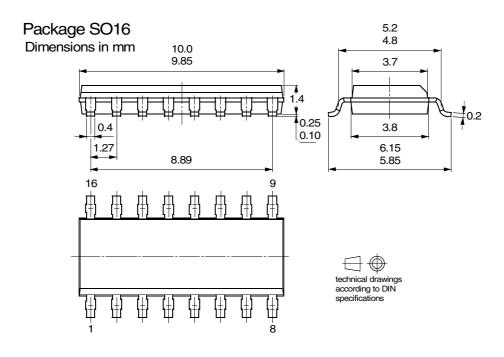
Figure 7-5. Application Circuit



8. Ordering Information

Extended Type Number	Package	Remarks
ATR4254-TBJY	SO16	_
ATR4254-TBQY	SO16	Taping corresponding to ICE-286-3
ATR4254-PEPY	QFN16	_
ATR4254-PEQY	QFN16	Taping corresponding to ICE-286-3

9. Package Information



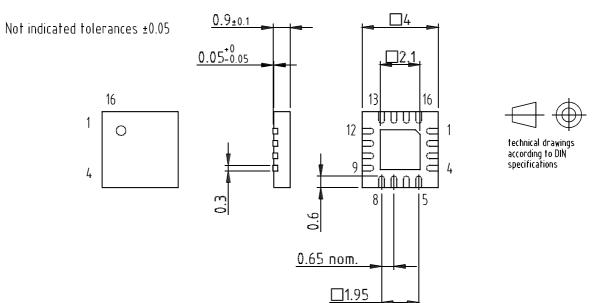




Package: QFN 16 - 4x4 Exposed pad 2.1x2.1

(acc. JEDEC OUTLINE No. MO-220)

Dimensions in mm



Drawing-No.: 6.543-5090.01-4

Issue: 2; 24.01.03



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